

## ATTY. DOCKET NO.

4495-2

**APPLICANT**

SUZUKI et al

FILING DATE

March 2, 2004

**SERIAL NO.**

10/790,238

EXAMINER

MURSALIN B. HAFIZ

**GROUP**

2814

(Use several sheets if necessary)

## U.S. PATENT DOCUMENTS

[illegible]

## FOREIGN PATENT DOCUMENTS

[illegible]

**OTHER DOCUMENTS** (including Author, Title, Date, Pertinent pages, etc.)

Mbh	Liu, "Electric-Pulse-Induced Reversible Resistance Change Effect in Magnetoresistive Films", Applied Physics Letters, Vol. 76, No. 19, 8 May 2000, American Institute of Physics, pp. 2749-2751
Mbh	Miyake, "Flash Memory vs. New Nonvolatile Memory, Part 2 (Flash Memory Overwhelming Stand-Alone, and New Promising "RRAM")", Nikkei Microdevices, January 2003, pp. 72-83 and partial English transmittal

\*Examiner

Date Considered

10/26/05

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

Form PTO-FB-A820 (Also PTO-1449)